

2024 IEEE International Reliability Physics Symposium (IRPS 2024)

**Grapevine, Texas, USA
14-18 April 2024**

Pages 1-471



**IEEE Catalog Number: CFP24RPS-POD
ISBN: 979-8-3503-6977-9**

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IEEE Catalog Number:	CFP24RPS-POD
ISBN (Print-On-Demand):	979-8-3503-6977-9
ISBN (Online):	979-8-3503-6976-2
ISSN:	1541-7026

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